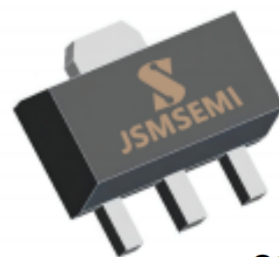


FEATURE

- Low $V_{CE(sat)}$
- Large current capacity


SOT-89

1. BASE
2. COLLECTOR
3. EMITTER

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	70	V
V_{CEO}	Collector-Emitter Voltage	70	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	3	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	$^{\circ}\text{C/W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

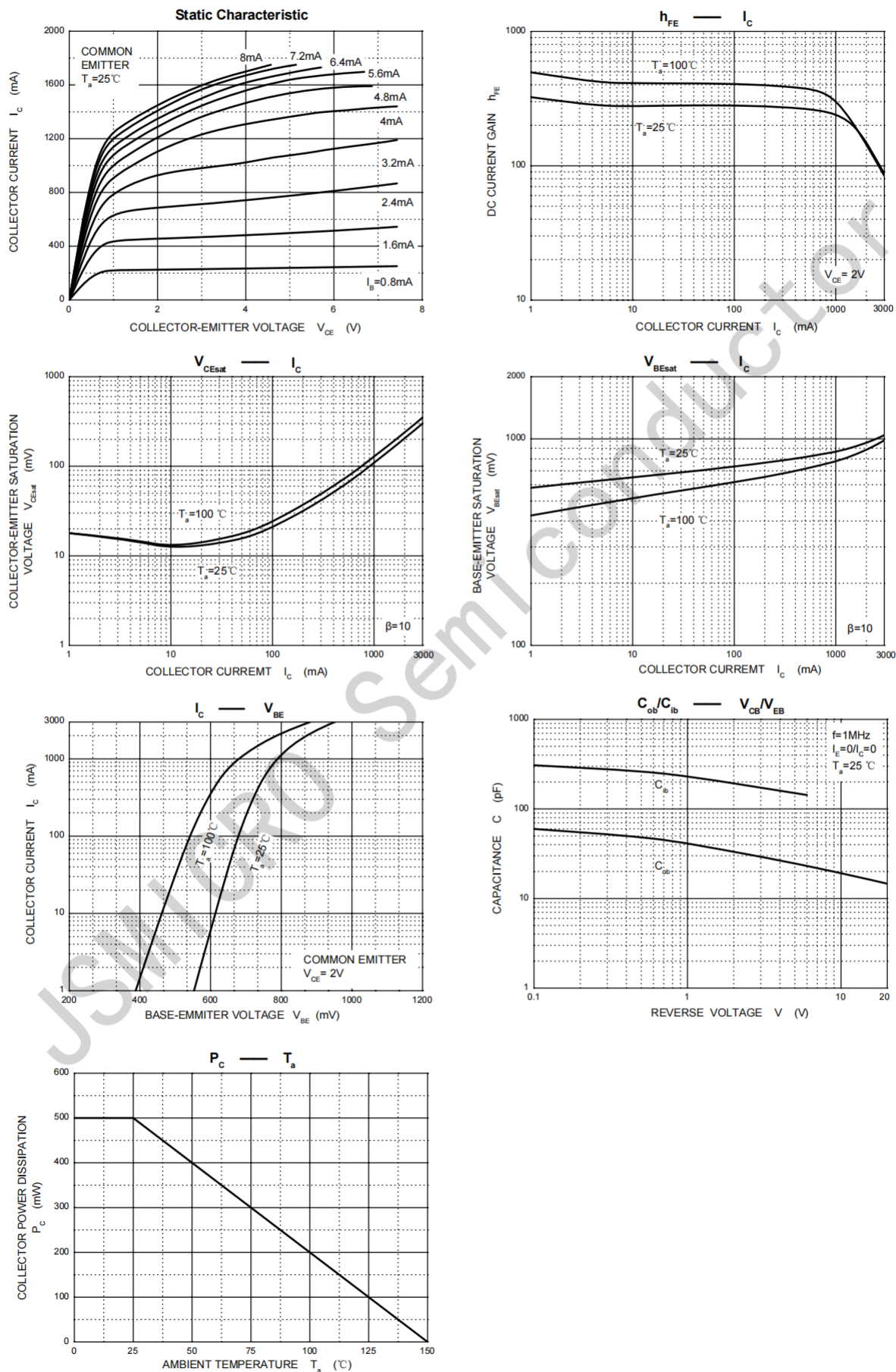
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	70			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}$, $I_B=0$	70			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}$, $I_E=0$			1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=30\text{V}$, $I_B=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}$, $I_C=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=2\text{V}$, $I_C=1\text{A}$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}$, $I_B=0.2\text{A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{A}$, $I_B=0.2\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{V}$, $I_C=0.1\text{A}$, $f=10\text{MHz}$	50			MHz

CLASSIFICATION of h_{FE}

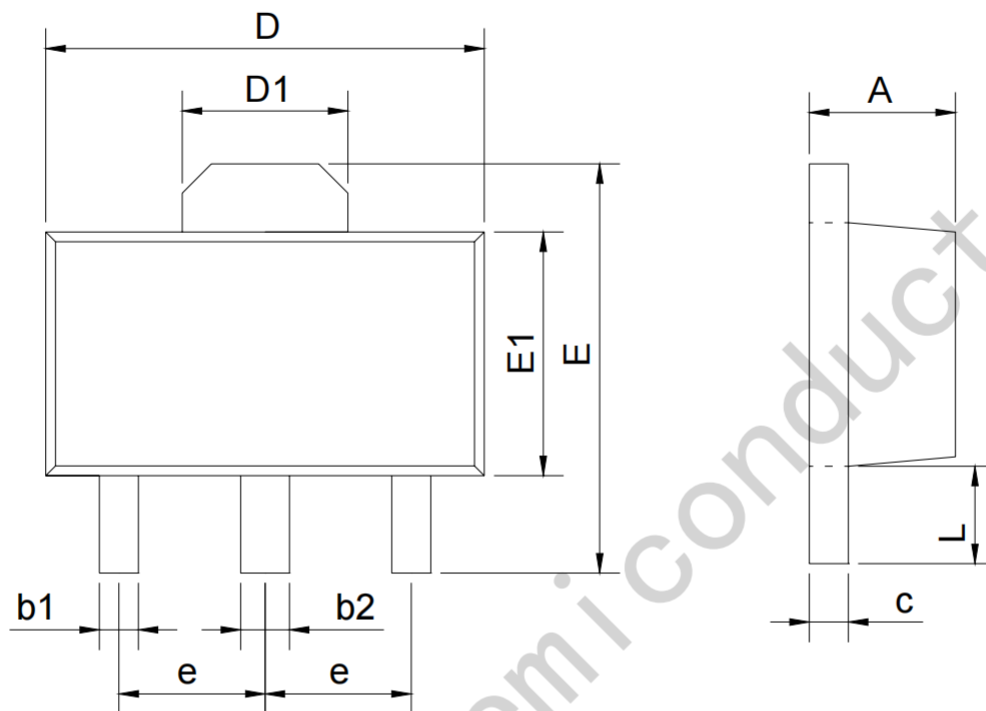
Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Typical Characteristics



Package Information

SOT-89



SYMBOL	mm	
	min	max
A	1.40	1.60
b1	0.35	0.50
b2	0.45	0.60
c	0.36	0.46
D	4.30	4.70
D1	1.40	1.80
E	4.00	4.40
E1	2.30	2.70
e	1.50BSC	
L	0.80	1.20